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| | Descrizione fisica | 1 online resource (194 p.) |
| | Collana | Diffusion and defect data. Part A, Diffusion and defect forum, , 1012-0386 ; ; v. 307 |
| | Altri autori (Persone) | FisherD. J |
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Phase Fluid Flow; Role of Silicon in PM Processed Soft Magnetic Alloy; Voltage Switch of Nano-Size Zinc Oxide Ceramic Defected Barium; Self-Diffusion in Nano-ZnO; Localised Vibrational Mode in CuO:Sn (5 at%) Nanoparticles; A Brief Survey of the Literature on Silica Refractory Research and Development: The Case for Nanostructured Silica Obtained from Rice Husk Ash (RHA) Local Density Diffusivity (LDD-) Model for Boron Out-Diffusion of In Situ Boron-Doped Si_{0.75}Ge_{0.25} Epitaxial Films Post Advanced Rapid Thermal Anneals with Carbon Co-ImplantGaAs Surface Composition Investigation during Al Thin Film Growth Using the CBE Method; Slow Positron Studies in Polymers; A Model and Simulated Analysis for Reliability and Failure in MEMS Fabrication; Abstracts; Keywords Index; Authors Index

Sommario/riassunto

This second volume in a new series covering entirely general results in the fields of defects and diffusion includes 356 abstracts of papers which appeared between the end of 2009 and the end of 2010. As well as the abstracts, the volume includes original papers on theory/simulation, semiconductors and metals: ""Predicting Diffusion Coefficients from First Principles ..."" (Mantina, Chen & Liu), ""Gouge Assessment for Pipes ..."" (Meliani, Pluvinage & Capelle), ""Simulation of the Impact Behaviour of ... Hollow Sphere Structures"" (Ferrano, Speich, Rimkus, Merkel & Ochsner), ""Elastic-Plastic
